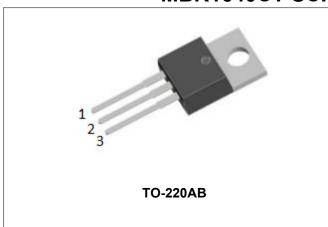






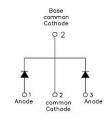
MBR1640CT SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings@Tc=25°C unless otherwise specified

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	40	V
Average Rectified Forward Current	I _{F (AV)}	Tc=134°C, In DC	8(Per Leg) 16(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	150	Α

Electrical Characteristics:

Characteristics	teristics Symbol Condition		Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V _{F1}	@ 16A, Pulse, T _J = 25 °C	0.71	0.85	V
	V _{F2}	@ 16A, Pulse, T _J = 125 °C	0.68	0.75	V
Reverse Current(Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25 °C	0.02	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 °C	12	15	mA
Junction Capacitance(Per Leg)	Ст	C_T @V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz		400	pF
Series Inductance(Per Leg)	Ls	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

^{*} Pulse width < 300 µs, duty cycle < 2%

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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	R _{th(j-c)}	DC operation	1.2	°C/W
Approximate Weight	wt	-	2	g
Case Style	TO-220AB			

10⁻²

Ratings and Characteristics Curves

Figure 1 Typical Forward Characteristics Instantaneous Forward Current -I_F(A) 125℃ 10¹ **25**℃ 10⁰ 0.6 1.0 1.2 Forward Voltage -V₋(V)

Instantaneous Reverse Current 4_R(mA) 10² **125**℃ 10¹ 10⁰ 10^{.1} 25℃

18

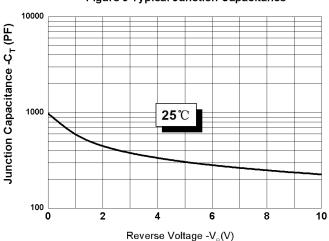
Figure 2 Typical Reverse Characteristics

Reverse Voltage -V_R(V) Figure 3 Typical Junction Capacitance

27

36

45



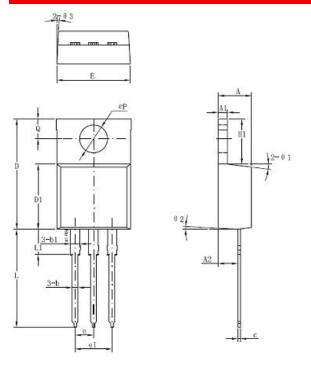
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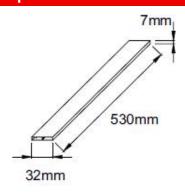


Mechanical Dimensions TO-220AB

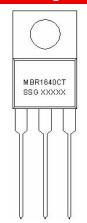


Symbol	Dimensions in millimeters			
	Min	Typical	Max	
Α	3.56	-	4.83	
A1	0.51	-	1.4	
A2	2.03	-	2.92	
b	0.38	-	1.02	
b1	1.14	-	1.78	
С	0.31	-	0.61	
D	14.22	-	16.51	
D1	8.38	-	9.42	
E	9.65	-	10.67	
е	-	2.54	-	
e1	-	5.08	-	
H1	5.84	-	6.86	
L	12.7	-	14.73	
L1	-	-	6.35	
ФР	_	3.56	-	
Q	2.54	-	3.43	

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

MBR = Device Type 16 = Forward Current (16A) 40 = Reverse Voltage(40V) CT = Configuration

CT = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information

Device	Package	Shipping	
MBR1640CT	TO-220AB (Pb-Free)	50 pcs/ tube	

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